

Multitopology High Power LED DC/DC Controller for Industrial Applications

# Datasheet

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# Multitopology High Power LED DC/DC Controller for Industrial Applications

#### ILD1151

#### ILD1151



## 1 Overview

#### Features

- Wide Input Voltage Range from 4.5 V to 45 V
- Constant Current or Constant Voltage Regulation
- Drives LEDs in Boost, Buck, Buck-Boost, SEPIC and Flyback Topology
- Very Low Shutdown Current:  $I_{q OFF} < 10 \ \mu A$
- Flexible Switching Frequency Range, 100 kHz to 500 kHz
- Synchronization with external clock source
- PWM Dimming
- · Analog Dimming feature to adjust average LED current
- Internal 5 V Low Drop Out Voltage Regulator
- Open Circuit Detection
- Short to GND Protection
- Output Overvoltage Protection
- Internal Soft Start
- Over Temperature Shutdown
- · Wide LED current range via simple adaptation of external components
- 300mV High Side Current Sense to ensure highest flexibility and LED current accuracy
- · Available in a small thermally enhanced PG-SSOP-14 package
- Green Product (RoHS) Compliant

#### Description

The ILD1151 is a Multitopology High Power DC/DC Controller IC with built in protection features. The main function of this device is to regulate a constant LED current. The constant current regulation is especially beneficial for LED color accuracy and longer lifetime. The controller concept of the ILD1151 allows multiple configurations such as Boost, Buck, Buck-Boost, SEPIC and Flyback by simply adjusting the external components. The ILD1151 offers the most flexible dimming options. Dimming can be achieved with analog or PWM input. The switching frequency is adjustable in the range of 100 kHz to 500 kHz and can be synchronized to an external clock source. The ILD1151 features an enable function reducing the shut-down current consumption to  $I_{q_OFF} < 10 \ \mu$ A. The current mode regulation scheme of this device provides a stable regulation loop maintained by small external compensation components. The integrated soft start feature limits the current peak as well as voltage overshoot at start-up. This IC provides output overvoltage protection, device overtemperature shutdown and short circuit to GND protection.

Туре	Package	Marking
ILD1151	PG-SSOP-14	ILD1151



PG-SSOP-14





Overview

#### Applications

- LED Controller for Industrial Applications
- Universal Constant Current and Voltage Source
- General Illumination e.g. Halogen Replacement
- Residential Architectural and Industrial Commercial Lighting for in- and outdoor
- Signal and Marker Lights for Orientation or Navigation (e.g. steps, exit ways, etc.)

For automotive and transportation applications, please refer to the Infineon® Auto LED products.



**Block Diagram** 

## 2 Block Diagram



Figure 1 Block Diagram



**Pin Configuration** 

## 3 Pin Configuration

## 3.1 Pin Assignment



## Figure 2 Pin Configuration

### 3.2 Pin Definitions and Functions

Pin	Symbol	Function
1	IVCC	Internal LDO Output; Used for internal biasing and gate drive. Bypass with external capacitor close to the pin. Pin must not be left open.
2	SWO	Switch Output; Connect to gate of external switching MOSFET
3	SGND	Current Sense Ground; Ground return for current sense switch
4	SWCS	Current Sense Input; Detects the peak current through switch
5	PWMO	PWM Dimming Output; Connect to gate of external MOSFET
6	FBH	Voltage Feedback Positive; Non inverting Input (+)
7	FBL	Voltage Feedback Negative; Inverting Input (-)
8	COMP	Compensation Input; Connect R and C network to pin for stability



#### **Pin Configuration**

Pin	Symbol	Function
9	OVFB	Output Overvoltage Protection Feedback;
		Connect to resistive voltage divider to set overvoltage threshold.
10	SET	Analog Dimming Input;
		Load current adjustment Pin. Pin must not be left open. If analog dimming feature is not used connect to IVCC pin.
11	FREQ / SYNC	Frequency Select or Synchronization Input;
		Connect external resistor to GND to set frequency.
		Or apply external clock signal for synchronization within frequency capture range.
12	GND	Ground;
		Connect to system ground.
13	EN / PWMI	Enable or PWM Input;
		Apply logic HIGH signal to enable device or PWM signal for dimming LED.
14	IN	Supply Input;
		Supply for internal biasing.
EP		Exposed Pad;
		Connect to external heatspreading GND Cu area (e.g. inner GND layer of multilayer PCB with thermal vias).



## 4 General Product Characteristics

### 4.1 Absolute Maximum Ratings

#### Absolute Maximum Ratings<sup>1)</sup>

 $T_{\rm j}$  = -40 °C to +125 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Pos.	Parameter	Symbol	Limi	t Values	Unit	Conditions	
			Min. Max.				
Voltage	es la	1			Į		
4.1.1	IN Supply Input	V <sub>IN</sub>	-0.3	45	V	-	
4.1.2	EN / PWMI Enable or PWM Input	V <sub>EN</sub>	-40	45	V	-	
4.1.3	FBH-FBL Feedback Error Amplifier Differential	$V_{\rm FBH}$ - $V_{\rm FBL}$	-40	61	V	The maximum delta must not exceed 61V	
4.1.4	FBH Feedback Error Amplifier Positive Input	V <sub>FBH</sub>	-40	61	V	The difference between $V_{FBH}$ and $V_{FBL}$ must not exceed 61V, refer to Parameter 4.1.3	
4.1.5	FBL Feedback Error Amplifier Negative Input	$V_{FBL}$	-40	61	V	The difference between $V_{FBH}$ and $V_{FBL}$ must not exceed 61V, refer to Parameter 4.1.3	
4.1.6	FBH and FBL current	$I_{\rm FBL,FBH}$	-	1	mA	t < 100ms, $V_{\text{FBH}}$ - $V_{\text{FBL}}$ = 0.3V	
4.1.7	OVFB	V <sub>OVP</sub>	-0.3	5.5	V	-	
4.1.8	Over Voltage Feedback Input		-0.3	6.2	V	<i>t</i> < 10s	
4.1.9	SWCS	V <sub>SWCS</sub>	-0.3	5.5	V	-	
4.1.10	Switch Current Sense Input		-0.3	6.2	V	<i>t</i> < 10s	
4.1.11	SWO	V <sub>SWO</sub>	-0.3	5.5	V	-	
4.1.12	Switch Gate Drive Output		-0.3	6.2	V	<i>t</i> < 10s	
4.1.13	SGND Current Sense Switch GND	V <sub>SGND</sub>	-0.3	0.3	V	-	
4.1.14	СОМР	V <sub>COMP</sub>	-0.3	5.5	V	-	
4.1.15	Compensation Input		-0.3	6.2	V	<i>t</i> < 10s	
4.1.16	FREQ / SYNC; Frequency and	V <sub>FREQ/SYNC</sub>	-0.3	5.5	V	-	
4.1.17	Synchronization Input		-0.3	6.2	V	<i>t</i> < 10s	
4.1.18	PWMO	V <sub>PWMO</sub>	-0.3	5.5	V	-	
4.1.19	PWM Dimming Output	-	-0.3	6.2	V	<i>t</i> < 10s	
4.1.20	SET	V <sub>SET</sub>	-0.3	45	V	-	
4.1.21	IVCC	V <sub>IVCC</sub>	-0.3	5.5	V	-	
4.1.22	Internal Linear Voltage Regulator Output		-0.3	6.2	V	<i>t</i> < 10s	
Tempe	ratures	1		I		1	
4.1.23	Junction Temperature	Tj	-40	150	°C	_	



#### **General Product Characteristics**

#### Absolute Maximum Ratings<sup>1)</sup>

 $T_j$  = -40 °C to +125 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values		Unit	Conditions
			Min.	Max.		
4.1.24	Storage Temperature	$T_{\rm stg}$	-55	150	°C	-
ESD S	usceptibility		L	i		
4.1.25	ESD Resistivity of all Pins	$V_{\rm ESD,HBM}$	-2	2	kV	HBM <sup>2)</sup>
4.1.26	ESD Resistivity of IN, EN/PWMI, FBH, FBL and SET pin to GND	V <sub>ESD,HBM</sub>	-4	4	kV	HBM <sup>2)</sup>

1) Not subject to production test, specified by design.

2) ESD susceptibility, Human Body Model "HBM" according to ANSI/ESDA/JEDEC JS-001 (1.5kΩ, 100pF)

- Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

#### 4.2 Functional Range

Pos.	Parameter Symbol		Lir	nit Values	Unit	Conditions	
			Min.	Max.			
4.2.1	Supply Voltage Range	V <sub>IN</sub>	4.5	45 <sup>1)</sup>	V	$V_{\rm IVCC}$ > $V_{\rm IVCC,RTH,d}$	
4.2.2	Feedback Voltage Input	$V_{FBH;} \ V_{FBL}$	3	60	V	-	
4.2.3	Junction Temperature	Tj	-40	125	°C	-	

1) Not subject to production test, specified by design.

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.



#### **General Product Characteristics**

### 4.3 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to www.jedec.org.

Pos.	Parameter	Symbol	I	Limit Val	ues	Unit	Conditions
		Min.	Тур.	Max.			
4.3.1	Junction to Case <sup>1) 2)</sup>	$R_{ m thJC}$	-	10	-	K/W	-
4.3.2	Junction to Ambient <sup>1) 3)</sup>	R <sub>thJA</sub>	_	47	_	K/W	2s2p
4.3.3		$R_{thJA}$	-	54	-	K/W	1s0p + 600 mm <sup>2</sup>
4.3.4		$R_{thJA}$	-	64	_	K/W	1s0p + 300 mm <sup>2</sup>

1) Not subject to production test, specified by design.

2) Specified RthJC value is simulated at natural convection on a cold plate setup (all pins and the exposed pad are fixed to ambient temperature). Ta=25°C; The IC is dissipating 1W.

3) Specified R<sub>thJA</sub> value is according to JEDEC 2s2p (JESD 51-7) + (JESD 51-5) and JEDEC 1s0p (JESD 51-3) + heatsink area at natural convection on FR4 board; The device was simulated on a 76.2 x 114.3 x 1.5 mm board. The 2s2p board has 2 outer copper layers (2 x 70µm Cu) and 2 inner copper layers (2 x 35µm Cu). A thermal via (diameter = 0.3 mm and 25 µm plating) array was applied under the exposed pad and connected the first outer layer (top) to the first inner layer and second outer layer (bottom) of the JEDEC PCB. Ta=25°C; The IC is dissipating 1W.



#### Switching Regulator

## 5 Switching Regulator

#### 5.1 Description

The ILD1151 regulator is suitable for Boost, Buck, Buck-Boost, SEPIC and Flyback configurations. The constant output current is especially useful for light emitting diode (LED) applications. The regulator function is implemented by a pulse width modulated (PWM) current mode controller.

The PWM current mode controller uses the peak current through the external power switch and error in the output current to determine the appropriate pulse width duty cycle (on time) for constant output current. The current mode controller provides a PWM signal to an internal gate driver which then outputs to an external n-channel enhancement mode metal oxide field effect transistor (MOSFET) power switch.

The current mode controller also has built-in slope compensation to prevent sub-harmonic oscillations which is a characteristic of current mode controllers operating at high duty cycles (>50% duty).

An additional built-in feature is an integrated soft start that limits the current through the inductor and external power switch during initialization. The soft start function gradually increases the inductor and switch current over  $t_{ss}$  (Parameter **5.2.8**) to minimize potential overvoltage at the output.



Figure 3 Switching Regulator Block Diagram



#### 5.2 Electrical Characteristics

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 1 EC Switching Regulator

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol	L	.imit Val	ues	Unit	Conditions	
			Min.	Тур.	Max.			
Regula	itor:		+					
5.2.1	Feedback Reference Voltage	V <sub>REF</sub>	0.29	0.30	0.31	V	refer to Figure 29 $V_{\text{REF}} = V_{\text{FBH}} - V_{\text{FBL}}$ $V_{\text{SET}} = 5\text{V}$ $I_{\text{LED}} = 350 \text{ mA}$	
5.2.2	Feedback Reference Voltage	V <sub>REF</sub>	0.057	0.06	0.063	V	refer to Figure 29 $V_{\text{REF}} = V_{\text{FBH}} - V_{\text{FBL}}$ $V_{\text{SET}} = 0.4 \text{V}$ $I_{\text{LED}} = 70 \text{mA}$	
5.2.3	Feedback Reference Voltage Offset	V <sub>REF_offset</sub>	-	-	5	mV	refer to Figure 17 and Figure 29 $V_{\text{REF}} = V_{\text{FBH}} - V_{\text{FBL}}$ $V_{\text{SET}} = 0.1V$ $V_{\text{OUT}} > V_{\text{IN}}$	
5.2.4	Voltage Load Regulation	$\begin{array}{c} (\Delta V_{REF}  / \\ V_{REF}  )  / \\ \Delta I_{BO} \end{array}$	-	-	5	%/A	refer to Figure 29 $V_{\text{SET}}$ = 5V; $I_{\text{LED}}$ = 100 to 500mA	
5.2.5	Switch Peak Over Current Threshold	V <sub>SWCS</sub>	130	150	170	mV	$V_{\text{FBH}} = V_{\text{FBL}} = 5V$ $V_{\text{COMP}} = 3.5V$	
5.2.6	Maximum Duty Cycle	$D_{\rm MAX, fixed}$	91	93	95	%	Fixed frequency mode	
5.2.7	Maximum Duty Cycle	D <sub>MAX,sync</sub>	88	-	-	%	Synchronization mode	
5.2.8	Soft Start Ramp	t <sub>SS</sub>	350	1000	1500	μs	$V_{\rm FB}$ rising from 5% to 95% of $V_{\rm FB}$ , typ.	
5.2.9	IFBH Feedback High Input Current	I <sub>FBH</sub>	38	46	54	μA	$V_{\rm FBH}$ - $V_{\rm FBL}$ = 0.3V	
5.2.10	IFBL Feedback Low Input Current	$I_{FBL}$	15	21	27	μA	$V_{\rm FBH}$ - $V_{\rm FBL}$ = 0.3V	
5.2.11	Switch Current Sense Input Current	I <sub>SWCS</sub>	10	50	100	μA	$V_{\rm SWCS}$ = 150mV	
5.2.12	Input Undervoltage Shutdown	$V_{\rm IN,off}$	3.5	-	4.5	V	$V_{\rm IN}$ decreasing	
5.2.13	Input Voltage Startup	$V_{\rm IN,on}$	-	-	4.85	V	$V_{\rm IN}$ increasing	

<sup>1)</sup> Not subject to production test, specified by design



#### **Switching Regulator**

#### Table 1EC Switching Regulator

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Values			nit Conditions
			Min.	Тур.	Max.		
Gate D	river for external Switch		<b>I</b>				
5.2.14	Gate Driver Peak Sourcing Current	I <sub>SWO,SRC</sub>	-	380	-	mA	$^{1)}V_{\rm SWO}$ = 1V to 4V
5.2.15	Gate Driver Peak Sinking Current	I <sub>SWO,SNK</sub>	-	550	-	mA	$^{1)}V_{\rm SWO}$ = 4V to 1V
5.2.16	Gate Driver Output Rise Time	t <sub>R,SWO</sub>	-	30	60	ns	$^{1)}C_{L,SWO}$ = 3.3nF; $V_{SWO}$ = 1V to 4V
5.2.17	Gate Driver Output Fall Time	t <sub>F,SWO</sub>	-	20	40	ns	$^{1)}C_{L,SWO}$ = 3.3nF; $V_{SWO}$ = 4V to 1V
5.2.18	Gate Driver Output Voltage	V <sub>SWO</sub>	4.5	-	5.5	V	$^{1)}C_{L,SWO} = 3.3nF;$

1) Not subject to production test, specified by design



#### **Oscillator and Synchronization**

## 6 Oscillator and Synchronization

#### 6.1 Description

The internal oscillator is used to determine the switching frequency of the boost regulator. The switching frequency can be selected from 100 kHz to 500 kHz with an external resistor to GND. To set the switching frequency with an external resistor the following formula can be applied.

$$R_{FREQ} = \frac{1}{\left(141 \times 10^{-12} \left[\frac{s}{\Omega}\right]\right) \times \left(f_{FREQ} \left[\frac{1}{s}\right]\right)} - \left(3.5 \times 10^{3} \left[\Omega\right]\right) \left[\Omega\right]$$

In addition, the oscillator is capable of changing from the frequency set by the external resistor to a synchronized frequency from an external clock source. If an external clock source is provided on the pin FREQ/SYNC, then the internal oscillator synchronizes to this external clock frequency and the boost regulator switches at the synchronized frequency. The synchronization frequency capture range is 250 kHz to 500 kHz.



Figure 4 Oscillator and Synchronization Block Diagram and Simplified Application Circuit



Figure 5 Synchronization Timing Diagram



#### 6.2 Electrical Characteristics

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 2 EC Oscillator and Synchronization

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Val	ues	Unit	Conditions
			Min.	Тур.	Max.		
Oscilla	itor:	-	- <u>!</u>				
6.2.1	Oscillator Frequency	$f_{\sf FREQ}$	250	300	350	kHz	$R_{\rm FREQ}$ = 20k $\Omega$
6.2.2	Oscillator Frequency Adjustment Range	$f_{\sf FREQ}$	100	-	500	kHz	
6.2.3	FREQ / SYNC Supply Current	$I_{FREQ}$	-	-	-700	μA	$V_{FREQ} = 0V$
6.2.4	Frequency Voltage	$V_{FREQ}$	1.16	1.24	1.32	V	$f_{\rm FREQ}$ = 100kHz
Synch	ronization	•	-	•			-
6.2.5	Synchronization Frequency Capture Range	$f_{\sf SYNC}$	250	-	500	kHz	-
6.2.6	Synchronization Signal High Logic Level Valid	V <sub>SYNC,H</sub>	3.0	-	-	V	1) 2)
6.2.7	Synchronization Signal Low Logic Level Valid	$V_{\rm SYNC,L}$	-	-	0.8	V	1) 2)
6.2.8	Synchronization Signal Logic High Pulse Width	t <sub>SYNC,PWH</sub>	200	-	-	ns	1) 2)
		1	1			1	1

1) Synchronization of external PWM ON signal to falling edge

2) Not subject to production test, specified by design



#### **Oscillator and Synchronization**

#### **Typical Performance Characteristics of Oscillator**

### Switching Frequency $f_{\rm SW}$ versus Frequency Select Resistor to GND $R_{\rm FREQ/SYNC}$





#### **Enable and Dimming Function**

## 7 Enable and Dimming Function

#### 7.1 Description

The enable function powers ON or OFF the device. A valid logic LOW signal on enable pin EN/PWMI powers OFF the device and current consumption is less than  $I_{q_OFF}$  (Parameter **7.2.14**). A valid logic HIGH enable signal on enable pin EN/PWMI powers on the device. The enable function features an integrated pull down resistor which ensures that the IC is shut down and the power switch is OFF in case the enable pin EN is left open.

In addition to the enable function described above, the EN/PWMI pin detects a pulse width modulated (PWM) input signal that is fed through to an internal gate driver. The internal gate driver outputs the same PWM signal on the PWMO pin to an external N-channel enhancement mode MOSFET for PWM dimming an LED load. PWM dimming an LED is a commonly practiced dimming method and can prevent color shift in an LED light source. Moreover the PWM output function may also be used to drive other types of loads besides LED.

The enable and PWM input function share the same pin. Therefore a valid logic LOW signal at the EN/PWMI pin needs to differentiate between an enable power OFF or an PWM dimming LOW signal. The device differentiates between enable OFF and PWM dimming signal by requiring the enable OFF at the EN/PWMI pin to stay LOW for the Enable Turn OFF Delay Time ( $t_{EN,OFF,DEL}$  Parameter **7.2.6**).



Figure 6 Block Diagram and Simplified Application Circuit Enable and LED Dimming



#### **Enable and Dimming Function**



Figure 7 Timing Diagram Enable and LED Dimming

#### 7.2 Electrical Characteristics

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 3EC Enable and Dimming

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
Enable	PWM Input:	I		4			
7.2.1	Enable/PWMI Turn On Threshold	$V_{\rm EN/PWMI,ON}$	3.0	-		V	-
7.2.2	Enable/PWMI Turn Off Threshold	$V_{EN/PWMI,OFF}$	-	-	0.8	V	-



#### **Enable and Dimming Function**

#### Table 3 EC Enable and Dimming

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol	Limit \	/alues		Unit	Conditions	
			Min.	Тур.	Max.			
7.2.3	Enable/PWMI Hysteresis	V <sub>EN/PWMI,HYS</sub>	50	200	400	mV	1)	
7.2.4	Enable/PWMI High Input Current	I <sub>EN/PWMI,H</sub>	-	-	30	μA	V <sub>EN/PWMI</sub> = 16.0V	
7.2.5	Enable/PWMI Low Input Current	$I_{\rm EN/PWMI,L}$	-	0.1	1	μA	$V_{\rm EN/PWMI}$ = 0.5V	
7.2.6	Enable Turn Off Delay Time	t <sub>EN,OFF,DEL</sub>	8	10	12	ms	-	
7.2.7	PWMI Min Duty Time	t <sub>PWMI,H</sub>	4	-	-	μs	-	
7.2.8	Enable Startup Time	t <sub>EN,START</sub>	100	-	-	μs	1)	
Gate D	river for Dimming Switch:			<b>I</b>				
7.2.9	PWMO Gate Driver Peak Sourcing Current	I <sub>PWMO,SRC</sub>	-	230	-	mA	<sup>1)</sup> $V_{\text{PWMO}}$ = 1V to 4V	
7.2.10	PWMO Gate Driver Peak Sinking Current	$I_{\rm PWMO,SNK}$	-	370	-	mA	<sup>1)</sup> $V_{\rm PWMO}$ = 4V to 1V	
7.2.11	PWMO Gate Driver Output Rise Time	t <sub>R,PWMO</sub>	-	50	100	ns	<sup>1)</sup> $C_{L,PWMO}$ = 3.3nF; $V_{PWMO}$ = 1V to 4V	
7.2.12	PWMO Gate Driver Output Fall Time	t <sub>F,PWMO</sub>	-	30	60	ns	<sup>1)</sup> $C_{L,PWMO}$ = 3.3nF; $V_{PWMO}$ = 4V to 1V	
7.2.13	PWMO Gate Driver Output Voltage	V <sub>PWMO</sub>	4.5	-	5.5	V	<sup>1)</sup> $C_{L,PWMO}$ = 3.3nF;	
Curren	t Consumption				U	1		
7.2.14	Current Consumption, Shutdown Mode	$I_{q\_OFF}$	-	-	10	μA	$V_{\text{EN/PWMI}} = 0.8 \text{ V};$ $T_{\text{i}} \le 105 \text{C}; V_{\text{IN}} = 16 \text{V}$	
7.2.15	Current Consumption, Active Mode <sup>2)</sup>	I <sub>q_ON</sub>	-	-	7	mA	$V_{\text{EN/PWMI}} \ge 4.75\text{V};$ $I_{\text{BO}} = 0\text{mA};$ $V_{\text{SWO}} = 0\%$ Duty Cycle	

1) Not subject to production test, specified by design

2) Dependency on switching frequency and gate charge of boost and dimming switch.



**Linear Regulator** 

## 8 Linear Regulator

#### 8.1 Description

The internal linear voltage regulator supplies the internal gate drivers with a typical voltage of 5V and current up to  $I_{LIM,min}$  (Parameter **8.2.2**). An external output capacitor with ESR lower than  $R_{IVCC,ESR}$  (Parameter **8.2.5**) is required on pin IVCC for stability and buffering transient load currents. During normal operation the external boost and dimming MOSFET switches will draw transient currents from the linear regulator and its output capacitor. Proper sizing of the output capacitor must be considered to supply sufficient peak current to the gate of the external MOSFET switches.

#### Integrated undervoltage protection for the external switching MOSFET:

An integrated undervoltage reset threshold circuit monitors the linear regulator output voltage ( $V_{IVCC}$ ) and resets the device in case the output voltage falls below the IVCC Undervoltage Reset switch OFF Threshold ( $V_{IVCC,RTH,d}$  Parameter 8.2.7). The Undervoltage Reset threshold for the IVCC pin helps to protect the external switches from excessive power dissipation by ensuring the gate drive voltage is sufficient to enhance the gate of an external logic level N-channel MOSFET.



Figure 8 Voltage Regulator Block Diagram and Simplified Application Circuit



#### 8.2 Electrical Characteristics

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 4EC Line Regulator

 $V_{IN}$  = 24V;  $T_j$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Values			Conditions	
			Min.	Тур.	Max.			
8.2.1	Output Voltage	V <sub>IVCC</sub>	4.85	5	5.15	V	$6V \le V_{IN} \le 45V$ $0.1 \text{mA} \le I_{IVCC} \le 50 \text{mA}$	
8.2.2	Output Current Limitation	I <sub>LIM</sub>	51	-	90	mA	$V_{\rm IN}$ = 13.5V $V_{\rm IVCC}$ = 4.5V	
8.2.3	Drop out Voltage	V <sub>DR</sub>	-	-	0.5	V	$V_{\rm IN}$ = 4.5V $I_{\rm IVCC}$ = 25mA	
8.2.4	IVCC Buffer Capacitor	CIVCC	0.47	1	100	μF	1) 2)	
8.2.5	IVCC Buffer Capacitor ESR	R <sub>IVCC,ESR</sub>	-	_	0.5	Ω	1)	
8.2.6	Undervoltage Reset Headroom		100	-	-	mV	$V_{\rm IVCC}$ decreasing $V_{\rm IVCC}$ - $V_{\rm IVCC,RTH,d}$	
8.2.7	IVCC Undervoltage Reset switch OFF Threshold	$V_{\rm IVCC,RTH,d}$	3.6	-	4.0	V	$^{\rm 3)}$ $V_{\rm IVCC}$ decreasing.	
8.2.8	IVCC Undervoltage Reset switch ON Threshold	V <sub>IVCC,RTH,i</sub>	-	-	4.5	V	$V_{\rm IVCC}$ increasing	

1) Not subject to production test, specified by design

2) Minimum value given is needed for regulator stability; application might need higher capacitance than the minimum.

3) Selection of external switching MOSFET is crucial and the  $V_{IVCC,RTH,d}$  min. as worst case  $V_{GS}$  must be considered.



## 9 Protection and Diagnostic Functions

#### 9.1 Description

The ILD1151 has integrated circuits to diagnose and protect against output overvoltage, open load, open feedback and overtemperature faults. Additionally the FBH and FBL potential is monitored and in case the LED load short circuits to GND (see description **Figure 15**) the regulator stops the operation and protects the system. In case any of the six fault conditions occur the PWMO and IVCC signal will change to an active logic LOW signal to communicate that a fault has occurred (detailed overview in **Figure 9** and **Figure 10** below). **Figure 11** illustrates the various open load and open feedback conditions. In case of an overtemperature condition the integrated thermal shutdown function turns off the gate drivers and internal linear voltage regulator. The typical junction shutdown temperature is  $175^{\circ}$ C (T<sub>j,SD</sub> Parameter **9.2.2**). After cooling down the IC will automatically restart. Thermal shutdown is an integrated protection function designed to prevent IC destruction and is not intended for continuous use in normal operation (**Figure 13**). To calculate the proper overvoltage protection resistor values an example is given in **Figure 14**.



Figure 9 Protection and Diagnostic Function Block Diagram



Input			Output		
Condition	Level*	SWO	PWMO	IVCC	
Overvoltage @	False	Sw*	H or Sw*	Active	
Output	True	L	L	Active	
OpenLoad	False	Sw*	H or Sw*	Active	
Open Load	True	L	L	Active	
Short to GND @ LED	False	Sw*	H or Sw*	Active	
chain	True	L	L	Active	
Open Feedback	False	Sw*	H or Sw*	Active	
Open reeuback	True	L	L	Active	
Overtemperature	False	Sw*	H or Sw*	Active	
Overtemperature	True	L	L	Shutdown	
Undervoltage @	False	Sw*	H or Sw*	Active	
Input	True	L	L	Shutdown	
*Note: Sw = Switching False = Condition does no True = Condition does ex					

### Figure 10 Diagnosis Truth Table



Figure 11 Open Load and Open Feedback Conditions



#### \_\_\_\_\_

ILD1151

#### **Protection and Diagnostic Functions**



Figure 12 Open load, Overvoltage and Overtemperature Timing Diagram





Figure 13 Device overtemperature protection behavior





Figure 14 Overvoltage Protection description

#### Short to GND protection for Highside Return Applications (B2B) from Figure 23

The FBH and FBL pins features a Short to GND detection threshold ( $V_{FBL,FBH_S2G}$ ). If the potential on those pins is below this threshold the Device stops his operation. This means that the PWMO signal changes to inactive state (LOW potential) and the corresponding p-channel ( $T_{DIM2}$ ) is switched OFF accordingly and protects the LED chain. For the B2B application some external components are needed to ensure a LOW potential during a short circuit event. D1 and D2 are low power diodes (BAS16-03W) and the resistor  $R_{lim}$  (10kOhm) is needed to limit the current through this path. The diode D3 should be a high power diode and is needed to protect the  $R_{FB}$  and the FBH and FBL pins in case of an short circuit to GND event. This short circuit detection and protection concept considers potential faults for LED chains (LED Modules) which are separated from the ECU via two wires (at the beginning and at the end of the LED chain). If the short circuit condition disappears, the device will re-start with a soft start.



Figure 15 Short Circuit to GND Protection



#### 9.2 **Electrical Characteristics**

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 5 **EC Protection and Diagnosis**

 $V_{\rm IN}$  = 24V;  $T_{\rm j}$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol	I	Limit Val	ues	Unit	Conditions	
			Min. Typ. Max.		Max.			
Short (	Circuit Protection			<b>I</b>			<u>+</u>	
9.2.1	FBH and FBL Short-Circuit fault sensing common mode range	V <sub>FBL,FBH_S2G</sub>	1.5	-	2	V	refer to Figure 15 $V_{\text{FBH}} = V_{\text{FBL}}$ decreasing	
Tempe	erature Protection:			<b>i</b>				
9.2.2	Over Temperature Shutdown	T <sub>j,SD</sub>	160	175	190	°C	<sup>1)</sup> refer to <b>Figure 13</b>	
9.2.3	Over Temperature Shutdown Hystereses	T <sub>j,SD,HYST</sub>	-	15	-	°C	1)	
Overvo	oltage Protection:		-				1	
9.2.4	Output Over Voltage Feedback Threshold Increasing	V <sub>OVFB,TH</sub>	1.21	1.25	1.29	V	refer to Figure 14	
9.2.5	Output Over Voltage Feedback Hysteresis	$V_{\rm OVFB,HYS}$	50	-	150	mV	<sup>1)</sup> Output Voltage decreasing	
9.2.6	Over Voltage Reaction Time	t <sub>OVPRR</sub>	2	-	10	μs	Output Voltage decreasing	
9.2.7	Over Voltage Feedback Input Current	I <sub>ovfb</sub>	-1	0.1	1	μA	V <sub>OVFB</sub> = 1.25V	
Open I	Load and Open Feedback Diagno	ostics			<b>I</b>			
9.2.8	Open Load/Feedback Threshold	V <sub>REF,1,3</sub>	-100	-	-20	mV	refer to Figure 11 $V_{\text{REF}} = V_{\text{FBH}} - V_{\text{FBL}}$ Open Circuit 1 or 3	
9.2.9	Open Feedback Threshold	V <sub>REF,2</sub>	0.5	-	1	V	$V_{\text{REF}} = V_{\text{FBH}} - V_{\text{FBL}}$ Open Circuit 2	

Specified by design; not subject to production test.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.



## 10 Analog Dimming

This pin is influencing the Feedback Voltage Error Amplifier by generating an internal current accordingly to an external reference voltage ( $V_{SET}$ ). If the analog dimming feature is not needed this pin must be connected to IVCC or external > 1.6V supply. Different application scenarios are described in **Figure 18**. This pin can also go outside of the ECU for instance if a thermistor is connected on a separated LED Module and the Analog Dimming Input is used to thermally protect the LEDs. For reverse battery protection of this pin an external series resistor should be placed to limit the current.

#### 10.1 Purpose of Analog Dimming:

1) It is difficult for LED manufacturers to deliver LEDs which have the same Brightness, Colorpoint and Forward Voltage Class. Due to this relatively wide spread of the crucial LED parameters customers order LEDs from one or maximum two different colorpoint classes. The LED manufacturer must preselect the LEDs to deliver the requested colorpoint class. Those preselected LEDs are matched in terms of the colorpoint but a variation of the brightness remains. To correct the brightness deviation an analog dimming feature is needed. The mean LED current can be adjusted by applying an external voltage V<sub>SET</sub> at the SET pin.

2) If the DC/DC application is separated from the LED loads the ECU manufacturers aim is to develop one hardware which should be able to handle different load current conditions (e.g. 80mA to 400mA) to cover different applications. To achieve this average LED current adjustment the analog dimming is a crucial feature.

#### 10.2 Description

Application Example:

Desired LED current = 400mA. For the calculation of the correct Feedback Resistor  $R_{FB}$  the following equation can be used: This formula is valid if the analog dimming feature is disabled and  $V_{SET} > 1.6V$ .

$$I_{LED} = \frac{V_{REF}}{R_{FB}} \implies R_{FB} = \frac{V_{REF}}{I_{LED}} \implies R_{FB} = \frac{0.3V}{400mA} = 750m\Omega$$

A decrease of the average LED current can be achieved by controlling the voltage at the SET pin ( $V_{SET}$ ) between 0V and 1.6V. The mathematical relation is given in the formula below:

$$I_{LED} = \frac{V_{SET} - 0, 1V}{5 * R_{FB}}$$

If  $V_{SET}$  is 100mV the LED current is only determined by the internal offset voltages of the comparators. For this example  $I_{LED} = 0A$  if  $V_{SET} < 100$ mV. Refer to the concept drawing in Figure 17.





Figure 16 Voltage V<sub>SET</sub> versus LED current



Figure 17 Concept Drawing Analog Dimming



#### Multi-purpose usage of the Analog dimming feature

**1)** A  $\mu$ C integrated digital analog converter (DAC) output or a stand alone DAC can be used to supply the SET pin of the ILD1151. The integrated voltage Regulator (V<sub>IVCC</sub>) can be used to supply the  $\mu$ C or external components if the current consumption does not exceed 25mA.

**2)** The analog dimming feature is directly connected to the input voltage of the system. In this configuration the LED current is reduced if the input voltage  $V_{IN}$  is decreasing. The DC/DC boost converter is changing (increasing) the switching duty cycle if  $V_{IN}$  drops to a lower potential. This is causing an increase of the input current consumption. If applications require a decrease of the LED current in respect to VIN variations this setup can be choosen.

**3)** The usage of an external resistor divider connected between IVCC (integrated 5V regulator output and gate buffer pin) SET and GND can be choosen for systems without  $\mu$ C on board. The concept allows to control the LED current via placing cheap low power resistors. Furthermore a temperature sensitive resistor (Thermistor) to protect the LED loads from thermal destruction can be connected additionally.

**4)** If the analog dimming feature is not needed the SET pin must be connected directly to >1.6V potential (e.g. IVCC potential)

**5)** Instead of an DAC the  $\mu$ C can provide a PWM signal and an external R-C filter is producing a constant voltage for the analog dimming. The voltage level is depending on the PWM frequency ( $f_{PWM}$ ) and duty cycle (DC) which can be controlled by the  $\mu$ c software after reading the coding resistor placed at the LED module.



#### **Analog Dimming**



Figure 18 Analog Dimming in various applications



#### **10.3 Electrical Characteristics**

All parameters have been tested at 25°C, unless otherwise specified.

#### Table 6 EC Analog Dimming

 $V_{\rm IN}$  = 24V;  $T_{\rm j}$  = -40 °C to +125 °C, all voltages with respect to ground, positive current flowing into pin; (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Values		Unit	Conditions
			Min.	Тур.	Max.		
Analog	Dimming Range						
10.3.1	SET programming range	VSFT	0	-	1.6	V	<sup>1)</sup> refer to <b>Figure 16</b>

1) Specified by design; not subject to production test.



#### **Application Information**

## 11 Application Information

Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.



Figure 19 Boost to Ground Application Circuit - B2G + Short Circuit protection (Boost configuration)

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
D <sub>1 - 10</sub>	White	Osram	LUW H9GP	LED	10
D <sub>BO</sub>	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	1
Dz	5V or 10V	Vishay	ZENER	Diode	1
D <sub>POL</sub>	80V Diode	Infineon	BAS1603W	Diode	1
$C_{IN,}C_{BO}$	100 uF, 50V	Panasonic	EEEFK1H101GP	Capacitor	2
C <sub>COMP</sub>	10 nF	EPCOS	X7R	Capacitor	1
CIVCC	1uF , 6.3V	EPCOS	MLCC CCNPZC105KBW X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC866	IC	1
L <sub>BO</sub>	100 uH	Coilcraft	MSS1278T-104ML	Inductor	1
R <sub>DIM1+2</sub> , R <sub>COMP</sub> , R <sub>POL</sub>	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	4
R <sub>FB</sub>	820 mΩ, 1%	Panasonic	ERJ14BQFR82U	Resistor	1
R <sub>FREQ</sub>	20 kΩ, 1%	Panasonic	ERJ3EKF2002V	Resistor	1
R <sub>OVH</sub>	33.2 kΩ, 1%	Panasonic	ERJ3EKF3322V	Resistor	1
R <sub>OVL</sub>	1 kΩ, 1%	Panasonic	ERJ3EKF1001V	Resistor	1
R <sub>cs</sub>	50 mΩ, 1%	Panasonic	ERJB1CFR05U	Resistor	1
T <sub>sw</sub>	100V N-ch, 35A	Infineon	IPG20N10S4L-22	Transistor	1
$T_{DIM1,}T_{DIM2}$	60V Dual N-ch (3.1A) and P-ch. enh. (2A)	Infineon	BSO615CG	Transistor	1
	alternativ: 100V N-ch (0.37A),	Infineon	BSP123	Transistor	1
	alternativ: 60V P-ch (1.9A)	Infineon	BSP171P	Transistor	1

Figure 20 Bill of Materials for B2G Application Circuit



#### **Application Information**



Figure 21 SEPIC Application Circuit (Buck-Boost configuration)

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
D <sub>1 - n</sub>	White	Osram	LUW H9GP	LED	variable
D <sub>BO</sub>	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	1
D <sub>POL</sub>	80V Diode	Infineon	BAS 1603W	Diode	1
C <sub>SEPIC</sub>	3.3 uF, 20V	EPCOS	X7R, Low ESR	Capacitor	1
$C_{\text{IN}}, C_{\text{BO}}$	100 uF, 50V	Panasonic	EEEFK1H101GP	Capacitor	2
C <sub>COMP</sub>	10 nF	EPCOS	X7R	Capacitor	1
CIVCC	1uF , 6.3V	EPCOS	X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC866	IC	1
$L_{1}, L_{2}$	47 uH	Coilcraft	MSS1278T-473ML	Inductor	2
	alternativ: 22uH coupled inductor	Coilcraft	MSD1278-223MLD	Inductor	1
$R_{\text{COMP},}R_{\text{POL}}$	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	2
$R_{FB}$	820 mΩ, 1%	Panasonic	ERJ14BQFR82U	Resistor	1
R <sub>FREQ</sub>	20 kΩ, 1%	Panasonic	ERJ3EKF2002V	Resistor	1
R <sub>OVH</sub>	33.2 kΩ, 1%	Panasonic	ERJ3EKF3322V	Resistor	1
R <sub>OVL</sub>	1 kΩ, 1%	Panasonic	ERJ3EKF1001V	Resistor	1
R <sub>cs</sub>	50 mΩ, 1%	Panasonic	ERJB1CFR05U	Resistor	1
$T_{\text{DIM}}, T_{\text{SW}}$	Dual N-ch enh. (60V, 20A)	Infineon	IPG20N06S4L-26	Transistor	1
	alternativ: 100V N-ch, 35A	Infineon	IPD35N10S3L-26	Transistor	2
	alternativ: 60V N-ch, 2.6A	Infineon	BSP318S	Transistor	2

Figure 22 Bill of Materials for SEPIC Application Circuit



#### **Application Information**



#### Figure 23 Flyback Application Circuit (Buck-Boost configuration)

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
D <sub>1 - n</sub>	White	Osram	LUW H9GP	LED	variable
D <sub>BO</sub>	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	1
C <sub>BO</sub>	3.3 uF, 50V (100V)	EPCOS	X7R, Low ESR	Capacitor	1
C <sub>IN</sub>	100 uF, 50V	Panasonic	EEEFK1H101GP	Capacitor	1
C <sub>COMP</sub>	47 nF	EPCOS	X7R	Capacitor	1
CIVCC	1 uF , 6.3V	EPCOS	X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC866	IC	1
L <sub>1</sub> , L <sub>2</sub>	1 µH / 9 uH	EPCOS	Transformer EHP 16	Inductor	1
R <sub>COMP</sub> , R <sub>POL</sub>	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	2
D <sub>POL</sub>	80 V Diode	Infineon	BAS 1603W	Diode	1
R <sub>FB</sub>	820 mΩ, 1%	lsabellenhütte	SMS – Power Resistor	Resistor	1
R <sub>FREQ</sub>	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	1
R <sub>ovh</sub>	56.2 kΩ, 1%	Panasonic	ERJ3EKF5622V	Resistor	1
R <sub>OVL</sub>	1.24 kΩ, 1%	Panasonic	ERJ3EKF1241V	Resistor	1
R <sub>cs</sub>	5 mΩ, 1%	lsabellenhütte	SMS - Power Resistor	Resistor	1
T <sub>DIM</sub> , T <sub>SW</sub>	Dual N-ch enh. (60V, 20A)	Infineon	IPG20N06S4L-26	Transistor	1
L	alternativ: 100V N-ch, 35A	Infineon	IPG20N10S4L-22	Transistor	2
	alternativ: 60V N-ch, 2.6A	Infineon	BSP318S	Transistor	2

Figure 24 Bill of Materials for Flyback Application Circuit



#### **Application Information**



Figure 25 Boost to Battery Application Circuit - B2B + Short Circuit protection (Buck-Boost config.)

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
D <sub>1 - n</sub>	White	Osram	LUW H9GP	Diode	variable
D <sub>BO</sub> , D <sub>3</sub>	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	2
D <sub>SC1</sub> , D <sub>SC2</sub>	Low Power Diode	Infineon	BAS 16-03W	Diode	2
Dz	Zener Diode			Diode	1
C <sub>BO</sub>	100 uF, 80V	Panasonic	EEVFK1K101Q	Capacitor	1
C <sub>IN</sub>	100 uF, 50V	Panasonic	EEEFK1H101GP	Capacitor	1
C <sub>COMP</sub>	10 nF	EPCOS	X7R	Capacitor	1
CIVCC	1 uF, 6.3V	EPCOS	MLCC CCNPZC105KBW X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC866	IC	1
L <sub>BO</sub>	100 uH	Coilcraft	MSS1278T-104ML_	Inductor	1
$R_{\text{COMP}}, R_{\text{DIM1}}, R_{\text{DIM2}}, R_{\text{lim}}$	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	4
R <sub>FB</sub>	820 mΩ, 1%	Panasonic	ERJ14BQFR82U	Resistor	1
R <sub>FREQ</sub>	20 kΩ, 1%	Panasonic	ERJ3EKF2002V	Resistor	1
R <sub>OVH</sub>	33.2 kΩ, 1%	Panasonic	ERJP06F5102V	Resistor	1
R <sub>ovl</sub>	1 kΩ, 1%	Panasonic	ERJ3EKF1001V	Resistor	1
R <sub>cs</sub>	50 mΩ, 1%	Panasonic	ERJB1CFR05U	Resistor	1
T <sub>DIM1</sub> ,T <sub>DIM2</sub>	60V Dual N-ch (3.1A) and P-ch. enh. (2A)	Infineon	BSO615CG	Transistor	1
	alternativ: 100V N-ch (0.37A),	Infineon	BSP 123	Transistor	1
	alternativ: 60V P-ch (1.9A)	Infineon	BSP171P	Transistor	1
T <sub>sw</sub>	N-ch, OptiMOS-T2 100V, 35A	Infineon	IPD35N10S3L-26	Transistor	1
	alternativ: 60V N-ch, 30A	Infineon	IPD30N06S4L-23	Transistor	1
	alternativ: 60V N-ch, 2.6A	Infineon	BSP318S	Transistor	1





#### **Application Information**



#### Figure 27 Buck Application Circuit + Short Circuit protection

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
D <sub>1 -2</sub>	White	Osram	LE UW Q9WP	LED	2
D <sub>BO</sub>	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	1
Dz	10V	Vishay	Zener Diode	Diode	1
D <sub>POL</sub>	80V Diode	Infineon	BAS1603W	Diode	1
C <sub>BO</sub>	4.7 uF, 50V	EPCOS	X7R	Capacitor	1
C <sub>IN</sub>	100 uF, 50V	Panasonic	EEEFK 1H101GP	Capacitor	1
C <sub>COMP</sub>	47 nF	EPCOS	X7R	Capacitor	1
CIVCC	1 uF , 6.3V	EPCOS	MLCC CCNPZC105KBW X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC866	IC	1
L <sub>1</sub>	22 µH	Coilcraft	MSS1278T	Inductor	1
$\begin{array}{c} R_{\text{DIM1+2},}R_{\text{COMP},}\\ R_{\text{POL}} \end{array}$	10 kΩ, 1%	Panasonic	ERJ3EKF1002V	Resistor	4
R <sub>FB</sub>	820 mΩ, 1%	lsabellenhütte	SMS – Power Resistor	Resistor	1
R <sub>FREQ</sub>	20 kΩ, 1%	Panasonic	ERJ3EKF2002V	Resistor	1
R <sub>cs</sub>	50 mΩ, 1%	lsabellenhütte	SMS - Power Resistor	Resistor	1
T <sub>DIM1</sub>	60V, 0.28A	Infineon	BSS 138	Transistor	1
T <sub>DIM2</sub>	-60V, -1.9A	Infineon	BSP 171	Transistor	1
T <sub>sw</sub>	30V, 22A	Infineon	IPB22N03S4L-15	Transistor	1
	alternativ: 60V N-ch, 2.6A	Infineon	BSP318S	Transistor	1





#### **Application Information**



Figure 29 Boost Voltage Application Circuit

Reference Designator	Value	Manufacturer	Part Number	Туре	Quantity
$D_{BO}$	Schottky, 3 A, 100 V <sub>R</sub>	Vishay	SS3H10	Diode	1
C <sub>BO</sub>	100 uF, 80V	Panasonic	EEVFK1K101Q	Capacitor	1
C <sub>IN</sub>	100 uF, 50V	Panasonic	EEEFK1H101GP	Capacitor	1
C <sub>COMP</sub>	10 nF	TBD	TBD	Capacitor	1
CIVCC	1 uF, 6.3V	Panasonic	MLCC CCNPZC105KBW X7R	Capacitor	1
IC <sub>1</sub>		Infineon	ILD1151	IC	1
IC <sub>2</sub>		Infineon	XC886	IC	1
L <sub>BO</sub>	100 uH	Coilcraft	MSS1278T-104ML_	Inductor	1
R <sub>COMP</sub>	10 kΩ	TBD	TBD	Resistor	1
$R_{FB1}, R_{FB3}$	51 kΩ, 1%	Panasonic	ERJ3EKF5102V	Resistor	1
$R_{FB2}$	1 kΩ, 1%	Panasonic	ERJ3EKF1001V	Resistor	1
R <sub>FREQ</sub>	20 kΩ, 1%	Panasonic	ERJ3EKF2002V	Resistor	2
R <sub>OVH</sub>	51 kΩ, 1%	Panasonic	ERJP06F5102V	Resistor	1
R <sub>OVL</sub>	1 kΩ, 1%	Panasonic	ERJ3EKF1001V	Resistor	1
R <sub>cs</sub>	50 mΩ, 1%	Panasonic	ERJB1CFR05U	Resistor	1
T <sub>sw</sub>	N-ch, 75 V, 65 mΩ	Infineon	IPD22N08S2L-50	Transistor	1

Figure 30 Bill of Materials for Boost Voltage Application Circuit

Note: This is a very simplified example of an application circuit. The function must be verified in the real application.



#### **Application Information**

### 11.1 Further Application Information

- For further information you may contact http://www.infineon.com/
- Application Note: ILD1150 / ILD1151 DC-DC Multitopology Controller IC for Industrial Applications "Dimensioning and Stability Guideline - Theory and Practice"



#### Package Outlines

## 12 Package Outlines



#### Figure 31 PG-SSOP-14

#### Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

For further package information, please visit our website: http://www.infineon.com/packages.



#### **Revision History**

## 13 Revision History

Revision	Date	Changes
1.0	2011-02-10	Initial Datasheet
1.1	2012-04-11	Page 3: RoHS Logo update
		Page 3: Topology update
		Application Information chapter update

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